

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 06-349855

(43)Date of publication of application : 22.12.1994

(51)Int.Cl.

H01L 21/336
H01L 29/784
G02F 1/136

(21)Application number : 05-160258

(71)Applicant : SEMICONDUCTOR ENERGY LAB CO LTD

(22)Date of filing : 04.06.1993

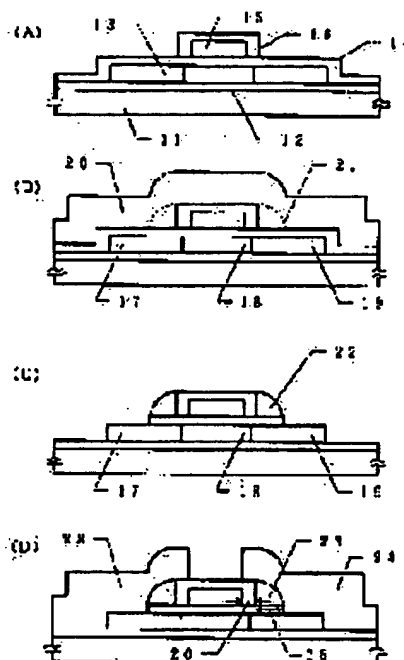
(72)Inventor : TERAMOTO SATOSHI
CHIYOU KOUYUU
TAKEMURA YASUHIKO

(54) SEMICONDUCTOR DEVICE AND ITS MANUFACTURE

(57)Abstract:

PURPOSE: To accurately form a contact hole in source/drain regions in a location close to a channel forming region by a method wherein substantially triangular insulated matter closely connected to an insulation layer in a gate electrode side surface is provided, whereby a contact location for the source/drain regions is specified.

CONSTITUTION: Substantially triangular insulated matter 22 closely connected to an insulation layer 16 in a gate electrode 15 side surface is provided, whereby a contact location for the source/drain regions 17, 19 is specified. For example, an Al film formed by a sputter method is patterned to form the gate electrode 15 and the surface is anode-oxidized to form the oxide layer 16. Next, impurities are doped onto a crystalline silicon film 13 by an ion implantation method and the source/drain regions 17, 19 are self-adjustably formed to form a silicon oxide film 20 by a sputter method. Next, anisotropic dry-etching is performed to leave the silicon oxide 22 formed in substantially a triangular form.



LEGAL STATUS

[Date of request for examination]

31.08.1999

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number] 3375681
[Date of registration] 29.11.2002
[Number of appeal against examiner's decision of rejection]
[Date of requesting appeal against examiner's decision of rejection]
[Date of extinction of right]

Copyright (C); 1998,2003 Japan Patent Office